

5. (Amended) The semiconductor device according to claim 1, wherein the extension section has an extension length identical with the width of the wiring.

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cont.
6. (Amended) The semiconductor device according to claim 1, wherein the extension section is square in its plan configuration.

7. (Amended) A semiconductor device having a wiring pattern formed by etching a conductive layer using a resist pattern as a mask, the semiconductor device comprising:

a contact section formed in an interlayer dielectric layer;

a first wiring formed over the interlayer dielectric layer and disposed with a minimum inter-wiring separation with respect to the contact section; and

a second wiring having a connection region to be connected to the contact section and extending in parallel with the first wiring,

wherein the connection region of the second wiring has a generally square plan configuration,

the second wiring has an extension section extending in a non-wiring region in the connection region, and

the extension section is disposed on sides of the connection region other than sides thereof facing the first wiring.

8. (Amended) A semiconductor device having a wiring pattern formed by etching a conductive layer using a resist pattern as a mask, the semiconductor device comprising:

a contact section formed in an interlayer dielectric layer;

a first wiring formed over the interlayer dielectric layer and disposed with a minimum inter-wiring separation with respect to the contact section; and

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a second wiring having a connection region to be connected to the contact section and extending in a direction perpendicular to the first wiring, wherein the connection region of the second wiring has a generally square plan configuration,

the second wiring has an extension section extending in a non-wiring region in the connection region, and

the extension section is disposed on sides of the connection region other than sides thereof facing the first wiring.

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13. (Amended) The semiconductor device according to claim 12, wherein the wiring is line-like in shape and has extension sections on three sides of the connection region.

14. (Amended) The semiconductor device according to claim 12, wherein the wiring is formed from the connection region and has extension sections on four sides of the connection region.

Please add new claims 21-26 as follows:

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21. (New) The semiconductor device according to claim 7, wherein the separation is shorter than a specified separation and there is a minimum separation between wirings in the wiring pattern.

22. (New) The semiconductor device according to claim 7, wherein the connection region is square in its plan configuration having dimensions that are greater than or equal to dimensions of the contact section.

23. (New) The semiconductor device according to claim 7, wherein the extension section has an identical width as a width of the wiring.

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24. (New) The semiconductor device according to claim 7, wherein the extension section has an extension length identical with the width of the wiring.

25. (New) The semiconductor device according to claim 8, wherein the separation is shorter than a specified separation and there is a minimum separation between wirings in the wiring pattern.

26. (New) The semiconductor device according to claim 8, wherein the connection region is square in its plan configuration having dimensions that are greater than or equal to dimensions of the contact section.
